



## STL34NF06

### N-CHANNEL 60V - 0.024Ω - 34A PowerFLAT™ LOW GATE CHARGE STripFET™II MOSFET

PRELIMINARY DATA

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STL34NF06	60 V	< 0.028Ω	34 A

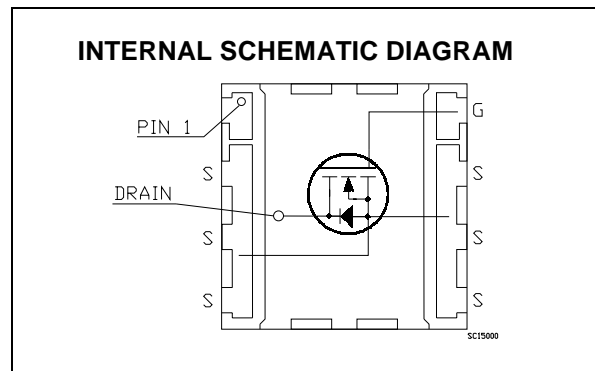
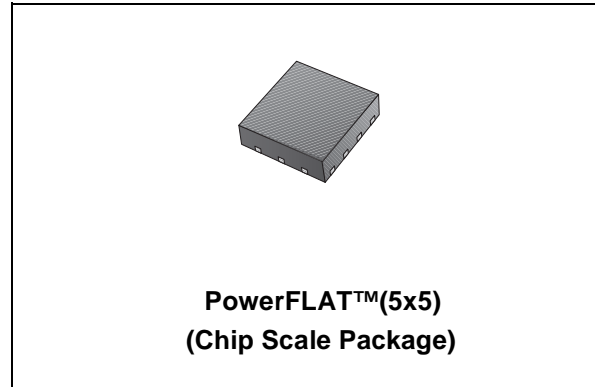
- TYPICAL R<sub>DS(on)</sub> = 0.024Ω
- IMPROVED DIE-TO-FOOTPRINT RATIO
- VERY LOW PROFILE PACKAGE

#### DESCRIPTION

This Power MOSFET is the second generation of STMicroelectronics unique "STripFET™" technology. The resulting transistor shows extremely low on-resistance and minimal gate charge. The new PowerFLAT™ package allow a significant reduction in board space without compromising performance.

#### APPLICATIONS

- DC-DC CONVERTERS
- BATTERY MANAGEMENT IN NOMADIC EQUIPMENT



#### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	60	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	60	V
V <sub>GS</sub>	Gate- source Voltage	± 20	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 25°C (*)	34	A
	Drain Current (continuous) at T <sub>C</sub> = 100°C	20	A
I <sub>DM</sub> (•)	Drain Current (pulsed)	136	A
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C	70	W
	Derating Factor	0.56	W/°C
E <sub>AS</sub> (1)	Single Pulse Avalanche Energy	250	mJ
T <sub>stg</sub>	Storage Temperature	-55 to 150	°C
T <sub>j</sub>	Max. Operating Junction Temperature		

(•) Pulse width limited by safe operating area

(1) Starting T<sub>j</sub> = 25°C, I<sub>D</sub> = 17A, V<sub>DD</sub> = 42V

(\*) Current Limited by Wire Bonding is 20A

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**STL34NF06****THERMAL DATA**

Rthj-case	Thermal Resistance Junction-case Max	1.8	°C/W
Rthj-pcb (#)	Thermal Resistance Junction-ambient Max	31.2	°C/W

(\*) When mounted on 1 inch<sup>2</sup> FR4 Board, 2oz of Cu, t ≤ 10 sec.

**ELECTRICAL CHARACTERISTICS (T<sub>CASE</sub> = 25 °C UNLESS OTHERWISE SPECIFIED)**

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0	60			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating, T <sub>C</sub> = 125 °C			1 10	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2			V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 17A		0.024	0.028	Ω

**DYNAMIC**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (1)	Forward Transconductance	V <sub>DS</sub> = 30 V, I <sub>D</sub> = 17 A		TBD		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, f = 1 MHz, V <sub>GS</sub> = 0		920		pF
C <sub>oss</sub>	Output Capacitance			225		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			80		pF

1. Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %.

**ELECTRICAL CHARACTERISTICS (CONTINUED)**  
**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 30V, I_D = 17 A$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 3)		11		ns
$t_r$	Rise Time			50		ns
$Q_g$	Total Gate Charge	$V_{DD} = 48V, I_D = 34 A,$ $V_{GS} = 10V$		32	43	nC
$Q_{gs}$	Gate-Source Charge			6.5		nC
$Q_{gd}$	Gate-Drain Charge			14.4		nC

**SWITCHING OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-Off-Delay Time	$V_{DD} = 30V, I_D = 17A,$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 3)		27		ns
$t_f$	Fall Time			11		ns

**SOURCE DRAIN DIODE**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD} (3)$	Source-drain Current				34	A
$I_{SDM} (2)$	Source-drain Current (pulsed)				136	A
$V_{SD} (1)$	Forward On Voltage	$I_{SD} = 34 A, V_{GS} = 0$			1.2	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 34 A, di/dt = 100A/\mu s,$ $V_{DD} = 10V, T_j = 150^\circ C$ (see test circuit, Figure 5)		63		ns
$Q_{rr}$	Reverse Recovery Charge			151		nC
$I_{RRM}$	Reverse Recovery Current			4.8		A

- Note: 1. Pulsed: Pulse duration = 300  $\mu s$ , duty cycle 1.5 %.  
 2. Pulse width limited by safe operating area.  
 3. Current Limited by Wire Bonding is 20A

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Fig. 1: Unclamped Inductive Load Test Circuit

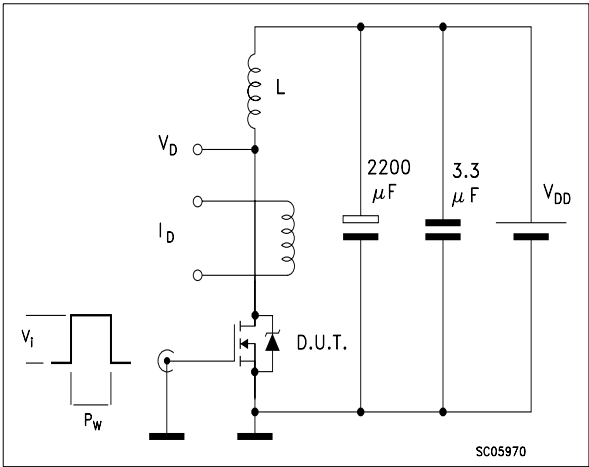


Fig. 2: Unclamped Inductive Waveform

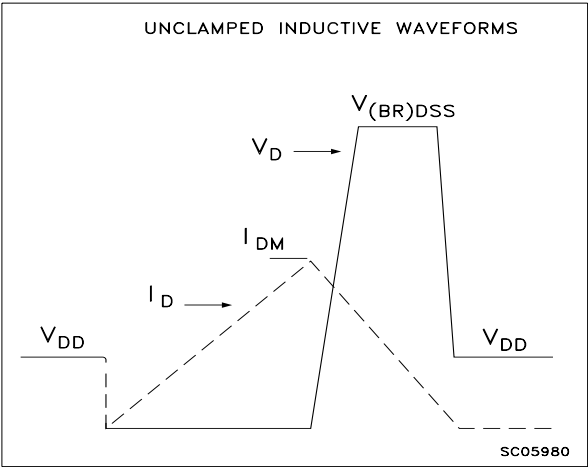


Fig. 3: Switching Times Test Circuit For Resistive Load

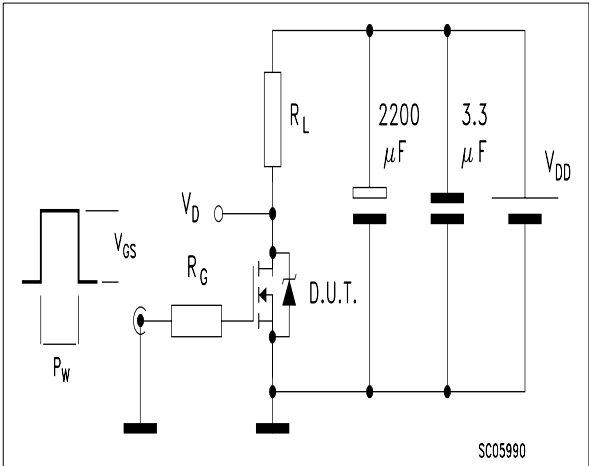


Fig. 4: Gate Charge test Circuit

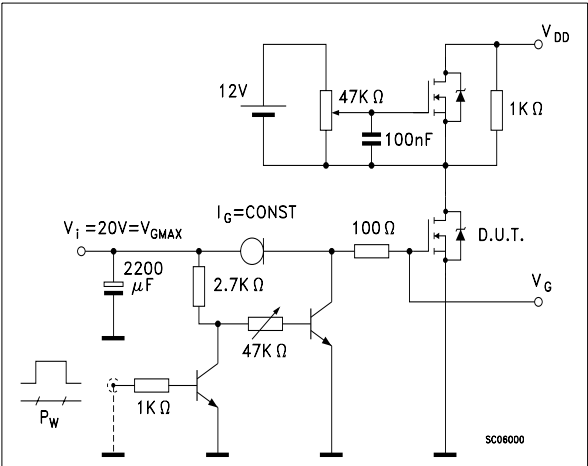
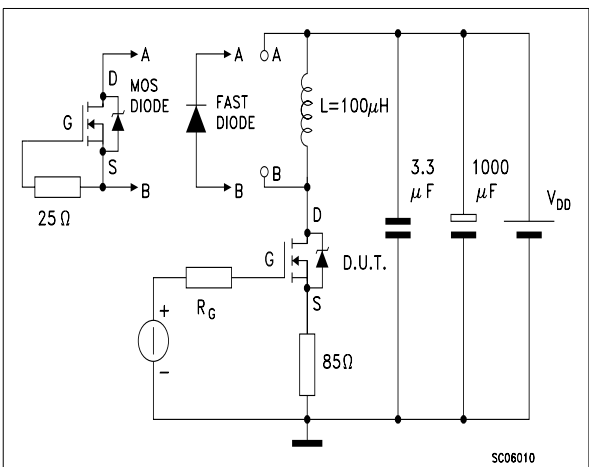
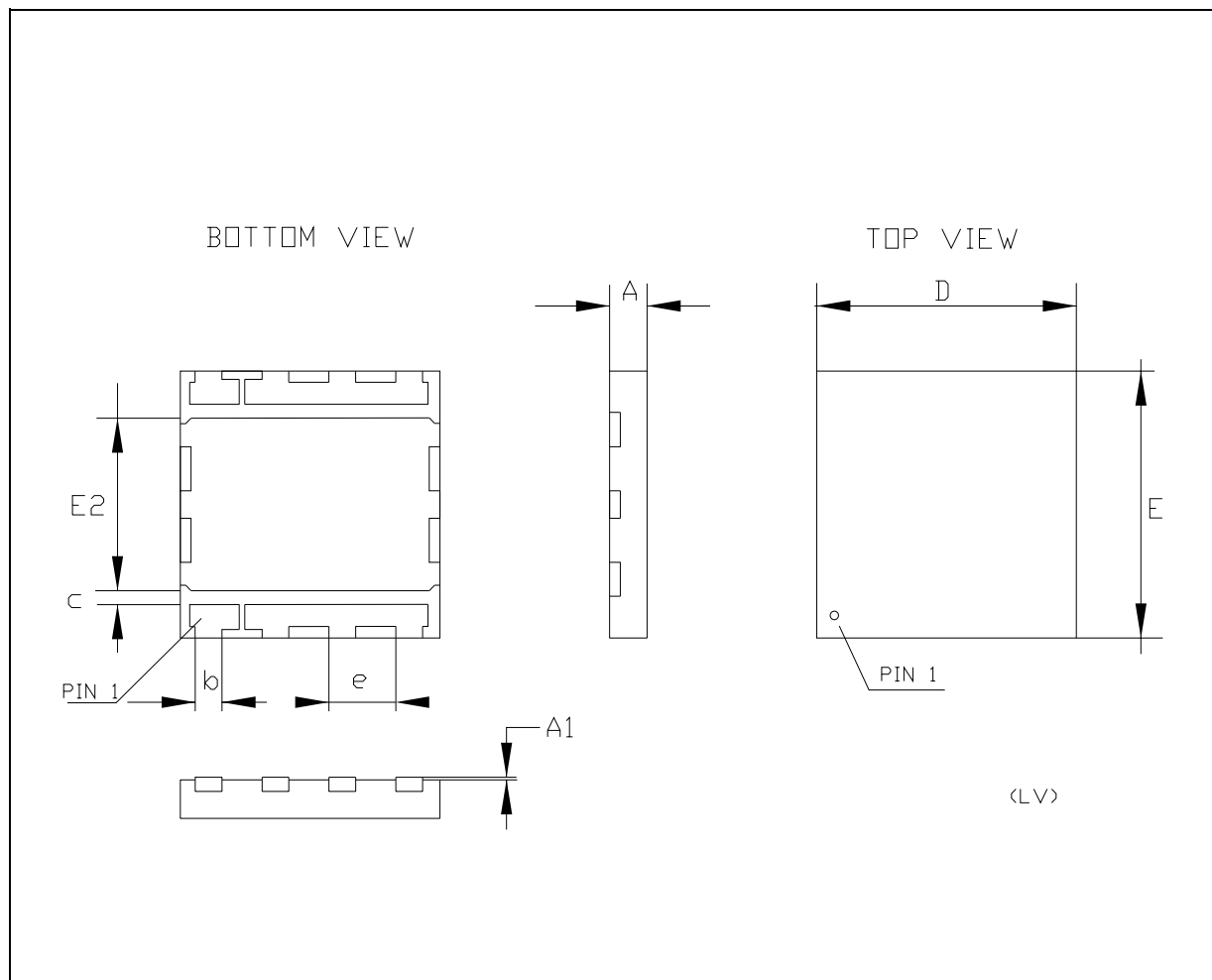


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



### PowerFLAT™(5x5) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A		0.90	1.00		0.035	0.039
A1		0.02	0.05		0.001	0.002
b	0.43	0.51	0.58	0.017	0.020	0.023
c	0.33	0.41	0.48	0.013	0.016	0.019
D		5.00			0.197	
E		5.00			0.197	
E2	3.10	3.18	3.25	0.122	0.125	0.128
e		1.27			0.050	



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